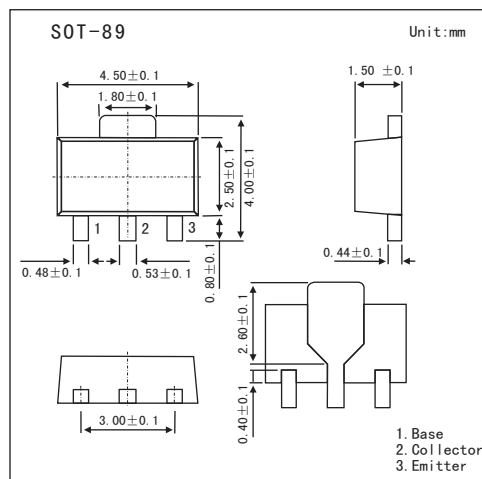


## 2SD1366A

### ■ Features

- Low frequency power amplifier



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	30	V
Collector-emitter voltage	V <sub>CE0</sub>	25	V
Emitter-base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>C</sub>	1	A
Total power dissipation	P <sub>C</sub> *	1	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* Value on the alumina ceramic board (12.5 × 20 × 0.7 mm)

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0	30			V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1 mA, I <sub>B</sub> = 0	25			V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10 μA, I <sub>C</sub> = 0	5			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = 250V, I <sub>B</sub> = 0			0.1	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 4 V, I <sub>C</sub> = 0			0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA	85		240	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 0.8 A, I <sub>B</sub> = 80mA			0.3	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 0.8 A, I <sub>B</sub> = 80mA			1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 2V, I <sub>C</sub> = 500mA		240		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		22		pF

### ■ hFE Classification

Marking	AC	AD
hFE	82~180	120~240